

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2242	(CMP or polish or polishing or planarize or planarizing) same (poly\$1silazane or per\$1hydrogenate\$1 or SOG)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 11:15
L2	52	(CMP or polish or polishing or planarize or planarizing) same (poly\$1silazane or per\$1hydrogenate\$1)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 11:15
L3	1833	1 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 11:16
L4	38	2 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 15:57
L5	13895	(peel or peeling or peelabl\$1) and ((heat or heating or bake or baking) with (water or steam or "H.sub.2 O"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 15:59
L6	2317	5 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 15:59
L7	384	6 and ((aluminum or alumina or "Al.sub.2 O.sub.3") with (heat or bake or baking or anneal or annealing))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 15:59
L8	14024	(peel or peeling or peelabl\$1) and ((heat or heating or bake or baking or anneal or annealing) with (water or steam or "H.sub.2 O"))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:00
L9	384	8 and 7	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:00
L10	298	9 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:00
L11	40	10 and (trench or isolation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:30
L12	298	10 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:01
L13	10	11 and (oxidizing or oxidation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:01

L14	15412	(aspect adj ratio) with (wide or width)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:31
L15	2723	(aspect adj ratio) with (wide or width) with depth	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:31
L16	2030	15 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:31
L17	681	16 and isolation	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:31
L18	507	17 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:31
L19	366	18 and trench	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:40
L20	795	438/691.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:40
L21	2301	438/692.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:40
L22	431	438/697.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:40
L23	3804	438/694.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:41
L24	1023	438/700.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:42
L25	257	Hieda-Katsuhiko.in.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:42
L26	67	Kawasaki-Atsuko.in.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:42
L27	70	Kiyotoshi-Masahiro.in.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:42
L28	101	Yamazaki-Soichi.in.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:43
L29	455	25 or 26 or 27 or 28	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:43

L30	7	29 and poly\$silazane	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 16:43
S10	12589	(STI or (trench near3 isolation)) and (CMP or polish or polishing or planarize or planarizing)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/24 11:14
S11	69	S10 and (poly\$1silazane or PSZ or "SiH.sub.2 NH") .	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/18 14:11
S12	34	S11 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/10/18 14:11